

## Amendments to the Claims

### Listing of Claims:

Claims 10-12 (canceled)

Claim 13 (new) A method for forming an embedded resistor comprising the steps of:  
depositing a thin film cermet material comprising  $M_xSi_yO_z$ ;  
where  $M = W$  or  $Ta$

said deposition onto a substrate is performed by co-sputtering of two targets: a  
first target of  $W$  or  $Ta$  and a second target of  $SiO_2$ ;

wherein sputtering of said  $SiO_2$  target is r.f. sputtering; and,  
deposition of the film on a substrate includes the steps of utilizing r.f. and d.c. magnetron  
sputtering with argon gas; and controlling the resistivity and TCR of the thin film cermet material  
by varying the sputtering power and pressure to obtain  $R_s$  and TCR values in accordance with the  
following table:

$R_s$ (ohms/Square)	TCR (ppm/C)	Pressure (mTorr)	Power (kW)
250	$\leq -200$	10	2.0
400	$\leq -220$	14	1.0
800	$\leq -260$	14	0.4
1500	$\leq -400$	18	0.4

Claim 14 (new) The invention according to claim 13 wherein said thin film cermet  
material is approximately 1000 angstroms thick.